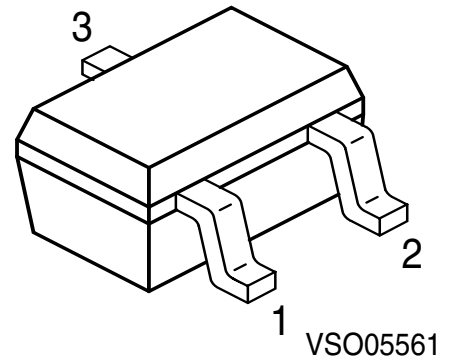


**NPN Silicon RF Transistor**

- Especially suitable for TV-Sat and UHF tuners



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

| Type    | Marking | Pin Configuration |       |       | Package |
|---------|---------|-------------------|-------|-------|---------|
| BF 775W | LOs     | 1 = B             | 2 = E | 3 = C | SOT-323 |

**Maximum Ratings**

| Parameter  | Symbol    | Value       | Unit |
|--|-----------|-------------|------|
| Collector-emitter voltage                                    | $V_{CEO}$ | 15          | V    |
| Collector-emitter voltage                                    | $V_{CES}$ | 20          |      |
| Collector-base voltage                                       | $V_{CBO}$ | 20          |      |
| Emitter-base voltage   | $V_{EBO}$ | 2.5         |      |
| Collector current  | $I_C$     | 30          | mA   |
| Base current   | $I_B$     | 4           |      |
| Total power dissipation<br>( $T_S \leq 86^\circ\text{C}^1$ ) | $P_{tot}$ | 280         | mW   |
| Junction temperature   | $T_j$     | 150         | °C   |
| Ambient temperature  | $T_A$     | -65 ... 150 |      |
| Storage temperature  | $T_{stg}$ | -65 ... 150 |      |

**Thermal Resistance**

| Parameter                  | Symbol     | Value      | Unit |
|----------------------------|------------|------------|------|
| Junction - soldering point | $R_{thJS}$ | $\leq 230$ | K/W  |

<sup>1</sup> $T_S$  is measured on the collector lead at the soldering point to the pcb

**Electrical Characteristics**

| Parameter   | Symbol        | Values |      |      | Unit          |
|---|---------------|--------|------|------|---------------|
|   |               | min.   | typ. | max. |               |
| <b>Characteristics</b>  |               |        |      |      |               |
| Collector-emitter breakdown voltage<br>$I_C = 1 \text{ mA}, I_B = 0$    | $V_{(BR)CEO}$ | 15     | -    | -    | V             |
| Collector-emitter cutoff current<br>$V_{CE} = 20 \text{ V}, V_{BE} = 0$ | $I_{CES}$     | -      | -    | 10   | $\mu\text{A}$ |
| Collector -base cutoff current<br>$V_{CB} = 10 \text{ V}, I_E = 0$      | $I_{CBO}$     | -      | -    | 100  | nA            |
| Emitter-base cutoff current<br>$V_{EB} = 2.5 \text{ V}, I_C = 0$        | $I_{EBO}$     | -      | -    | 100  | $\mu\text{A}$ |
| DC current gain<br>$I_C = 10 \text{ mA}, V_{CE} = 8 \text{ V}$          | $h_{FE}$      | 40     | 100  | 200  | -             |

**Electrical Characteristics**

| Parameter   | Symbol        | Values |            |        | Unit |
|---|---------------|--------|------------|--------|------|
|   |               | min.   | typ.       | max.   |      |
| <b>AC Characteristics</b>   |               |        |            |        |      |
| Transition frequency<br>$I_C = 10 \text{ mA}, V_{CE} = 8 \text{ V}, f = 500 \text{ MHz}$  | $f_T$         | 3.5    | 5.5        | -      | GHz  |
| Collector-base capacitance<br>$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$  | $C_{cb}$      | -      | 0.4        | 0.6    | pF   |
| Collector emitter capacitance<br>$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}$   | $C_{ce}$      | -      | 0.25       | -      |      |
| Emitter-base capacitance<br>$V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$   | $C_{eb}$      | -      | 0.5        | -      |      |
| Noise figure<br>$I_C = 2 \text{ mA}, V_{CE} = 6 \text{ V}, Z_S = Z_{Sopt},$<br>$f = 900 \text{ MHz}$<br>$f = 1.8 \text{ GHz}$   | $F$           | -<br>- | 1<br>1.6   | -<br>- | dB   |
| Power gain, maximum available <sup>F)</sup><br>$I_C = 10 \text{ mA}, V_{CE} = 8 \text{ V}, Z_S = Z_{Sopt},$<br>$Z_L = Z_{Lopt}, f = 900 \text{ MHz}$<br>$f = 1.8 \text{ GHz}$ | $G_{ma}$      | -<br>- | 17<br>11.5 | -<br>- |      |
| Transducer gain<br>$I_C = 10 \text{ mA}, V_{CE} = 8 \text{ V}, Z_S = Z_L = 50\Omega,$<br>$f = 900 \text{ MHz}$<br>$f = 1.8 \text{ GHz}$                                       | $ S_{21e} ^2$ | -<br>- | 13.5<br>8  | -<br>- |      |

$$^1G_{ma} = |S_{21}/S_{12}| (k - (k^2 - 1)^{1/2})$$